

REMARKS

Favorable reconsideration of this application is respectfully requested.

Initially, applicants and applicants' representative thank Examiner Cao for the interview granted applicants' representative on January 8, 2006. During the interview the outstanding rejections were discussed in detail and applicants' representative pointed out differences between the present invention and the applied art. Also, during the interview claim amendments to clarify certain claim features were discussed. The present response submits those discussed claim amendments. During the interview the Examiner indicated such amended claims appear to address the outstanding rejections.

Claims 1-12, 14-18, and 20 are pending in this application. Claims 1-12 and 14-18 were rejected under 35 U.S.C. § 102(b) as anticipated by U.S. patent 5,714,775 to Inoue et al. (herein "Inoue"). Claim 20 was rejected under 35 U.S.C. § 103(a) as unpatentable over Inoue. Those rejections are traversed by the present response as discussed next.

Each of the independent claims is amended by the present response to clarify features therein. Specifically, independent claim 1 now recites:

a source region continuously connecting at one end with the source diffused layers for electrically interconnecting the first gate electrode group and the source contact.
[Emphasis added].

The other independent claims 3, 4, and 11 are amended to recite similar features. Those claim features are believed to clearly distinguish over Inoue.

According to features recited in the claims, and with reference to Figures 7-9 in the present specification as a non-limiting example, a source region 26 at one end continuously connects with the source diffused layers 14, see Figure 9 showing at the top therein the source region 26 continuously connecting with the source diffused layers 14. Further, the source diffused layer 14 connects with the source contact 24 via the source region 26.

Thereby, in the claimed structure the source diffused layer 14 are connected to the source region 26, and the source region is connected with the source contact 24. Accordingly, electric charges flowing from the source diffused layers 14 are passed through the source region 26 to reach the source contact 24.

With such a claimed structure the device resistance of the MOSFET according to a structure in the claimed invention can be set low as a result of the device configuration.

Applicants respectfully submit Inoue does not disclose or suggest particularly the claim structure of “a source region continuously connecting at one end with the source diffused layer for electrically interconnecting the first gate electrode group and the source contact”.

The outstanding rejection cites Inoue to disclose a source diffused region 28, a source contact having a portion 42, and source regions 34/45. In Inoue the noted source diffused region 38 is in fact an emitter region and the noted source region 34/45 is a P-type base structure, and a p-n junction is generated at the boundary between the source diffused region 38 and the source regions 34/45. That is, the region having the noted source diffused region 38 and the source regions 34/45 is not constituted of an interconnection by a N-type diffusion layer, but instead is a semiconductor element, which indicates a bipolar transistor.

In contrast to the claims as written, in Inoue the noted source regions 34/45 are *not* continuously connected at one end with the source diffused layer 38. In noted Figure 14 in Inoue each of the noted source regions 34/45 and source diffused layer 38 are only formed between the gate electrode group 35. There is no continuous connecting of a source region in Inoue. Again with reference to Figure 9 in the present specification as a non-limiting example, in the claimed invention a source region 26 at one end continuously connects with source diffused layers 14 (see the top end of the device in Figure 9). Inoue clearly does not disclose or suggest such a structure.

In such ways, the claims as written positively recite features neither taught nor suggested by Inoue, and thereby the claims as written distinguish over Inoue.

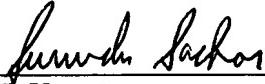
As no other issues are pending in this application, it is respectfully submitted that the present application is now in condition for allowance, and it is hereby respectfully requested that this case be passed to issue.

Respectfully submitted,

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